

DOCKET NO.: 205890US99



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: : GROUP ART UNIT: 2811

JAMAL RAMDANI ET AL :

SERIAL NO.: 09/721,566 : EXAMINER: HU, S.

FILED: NOVEMBER 22, 2000 :

FOR: STRUCTURE AND METHOD FOR FABRICATING SEMICONDUCTOR  
STRUCTURES AND DEVICES UTILIZING THE FORMATION OF A  
COMPLIANT SUBSTRATE FOR MATERIALS USED TO FORM THE SAME

#10  
9/5/02  
JUR

RESTRICTION RESPONSE

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

RECEIVED  
AUG 21 2002  
TECHNOLOGY CENTER 2811

Responsive to the Restriction Requirement dated April 19, 2002, Applicants elect  
from Species 1 and 2 the Zintl type phase material and further elect the condition wherein the  
oxide buffer layer is converted into an amorphous oxide.

REMARKS

The claims have been divided into allegedly distinct species. Applicant has elected  
the Zintl type phase material and the oxide buffer layer converted into an amorphous oxide.  
Applicant cannot determine from the Office Letter which Claims the Examiner indicates such  
election will read on ("claims 1, 17-27, but within claims 1-4 and 15-27"). The  
restriction/election requirement is traversed.

The Office Letter contains absolutely no basis for the requirement. This is manifestly